



150V 45mΩ N-Ch Power MOSFET

Features

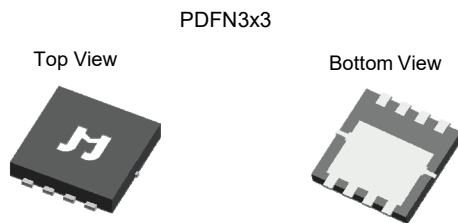
- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- 100% UIS Tested, 100% R_g Tested

Product Summary

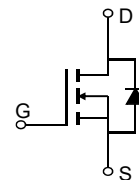
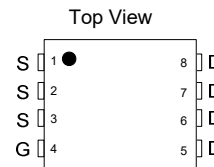
Parameter	Value	Unit
V_{DS}	150	V
$V_{GS(th_Typ)}$	3.2	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	15	A
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 10V$)	45	mΩ

Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems
- Motor Driving in Power Tool, E-vehicle, Robotics



Pin Configuration

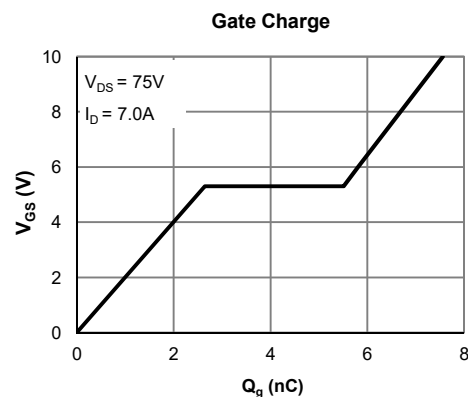
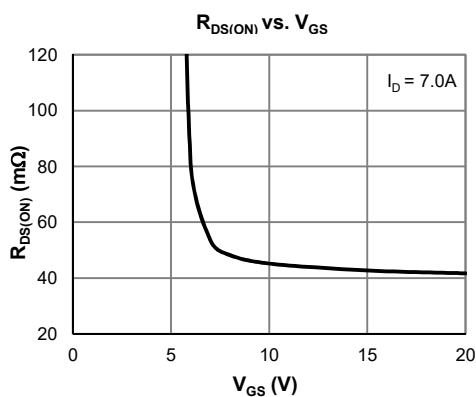


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1552AU-13	PDFN3x3	8	SH1552A	1	-55 to 150	13-inch Reel	3000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	150	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	15
		$T_C = 100^\circ C$	9.4
Pulsed Drain Current ⁽²⁾	I_{DM}	40	A
Avalanche Current ⁽³⁾	I_{AS}	16	A
Avalanche Energy ⁽³⁾	E_{AS}	13	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	28
		$T_C = 100^\circ C$	11
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

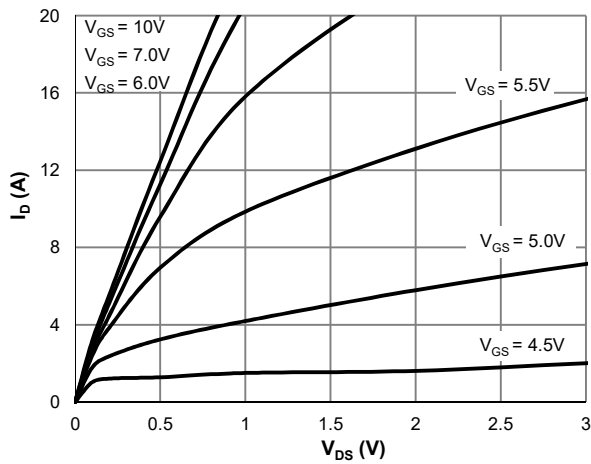
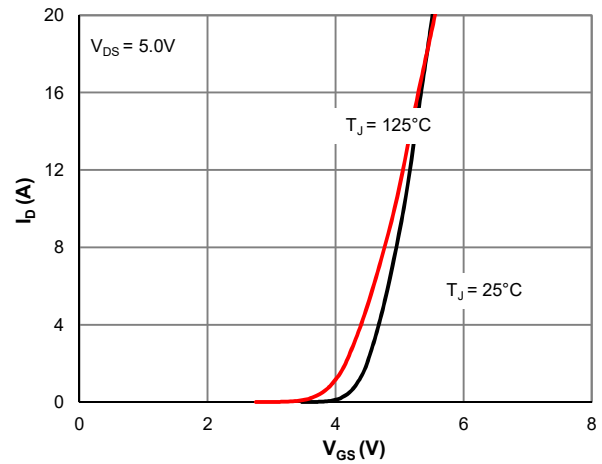
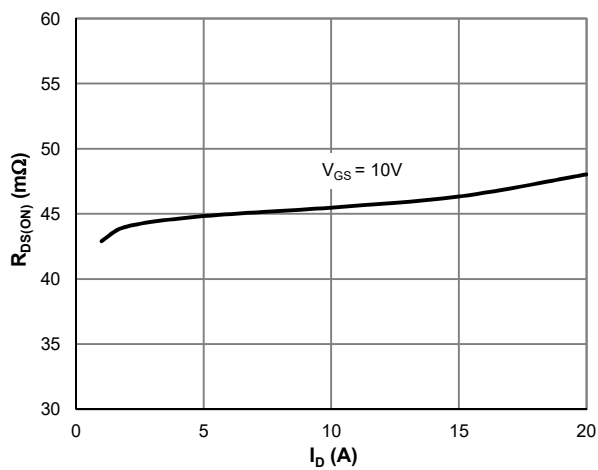
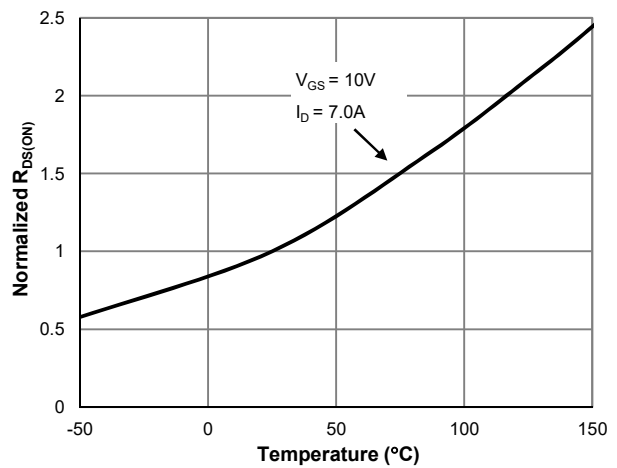
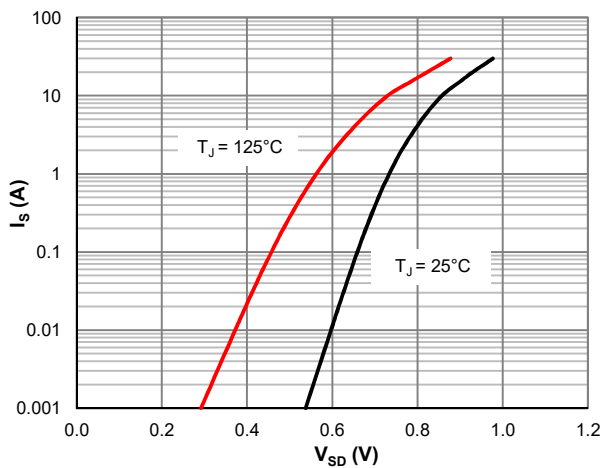
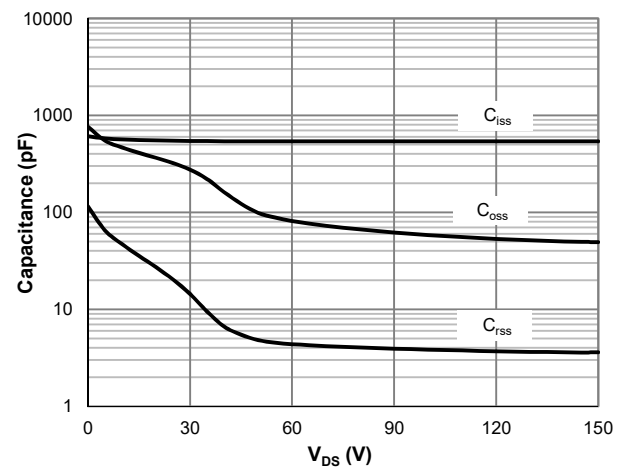
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	150			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.2	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 7\text{A}$		45	52	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 7\text{A}$		15		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.73	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			28	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 75\text{V}, f = 1\text{MHz}$		540		pF
Output Capacitance	C_{oss}			69		pF
Reverse Transfer Capacitance	C_{rss}			4.1		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		1.1		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 75\text{V}, I_D = 7\text{A}$		7.6		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			5.8		nC
Gate Source Charge	Q_{gs}			2.7		nC
Gate Drain Charge	Q_{gd}			2.9		nC
Turn-On Delay Time	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$ $R_L = 10\Omega, R_{GEN} = 6\Omega$		11		ns
Turn-On Rise Time	t_r			18		ns
Turn-Off Delay Time	$t_{D(off)}$			20		ns
Turn-Off Fall Time	t_f			6.1		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 7\text{A}, dI_F/dt = 100\text{A}/\mu\text{S}$		68		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 7\text{A}, dI_F/dt = 100\text{A}/\mu\text{S}$		95		nC

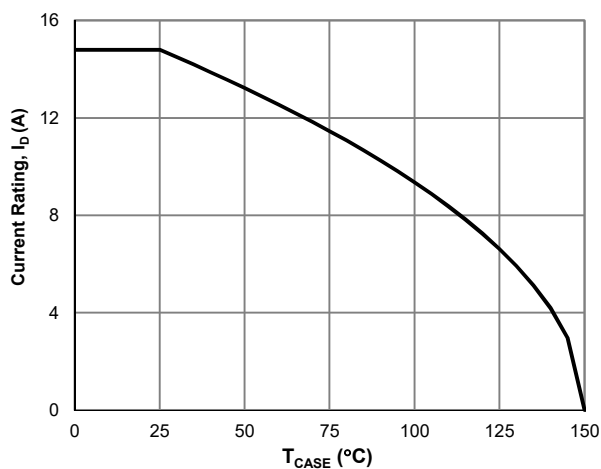
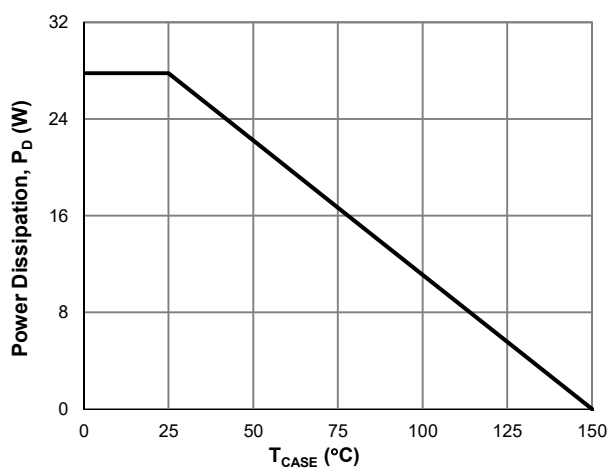
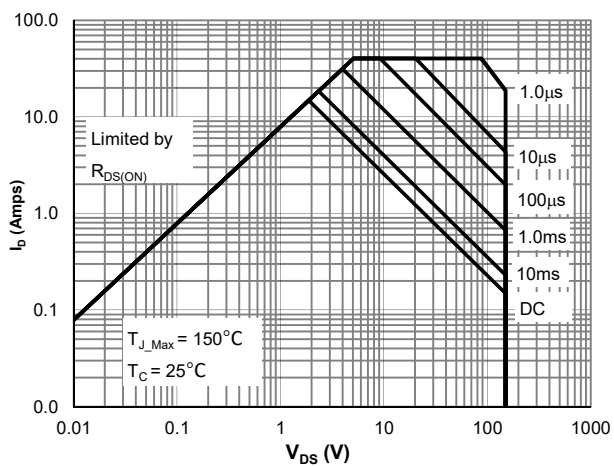
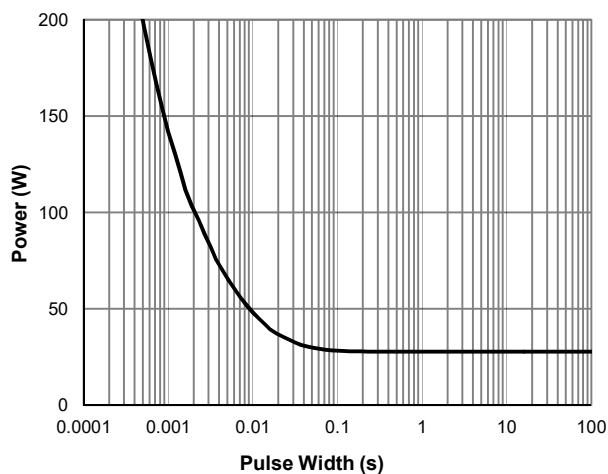
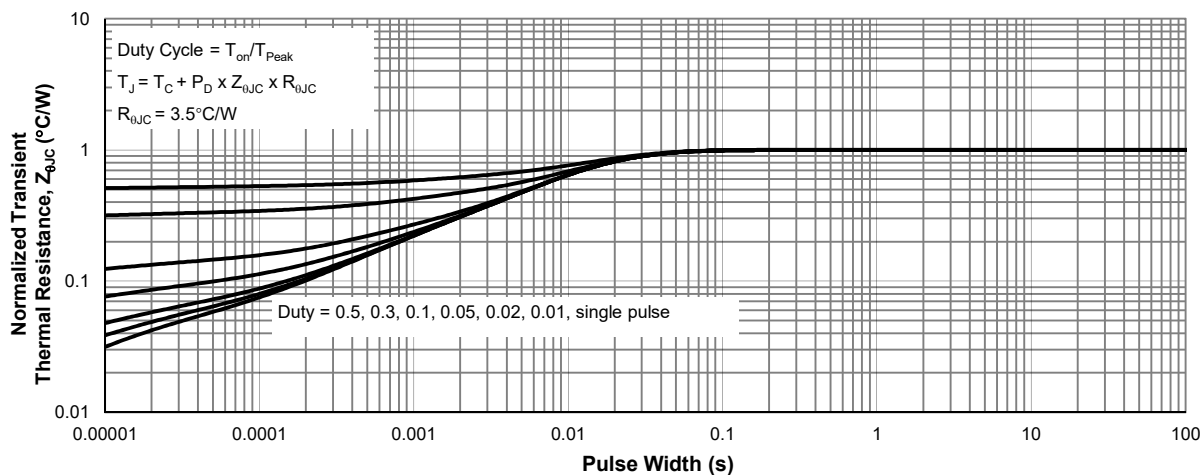
Thermal Performance

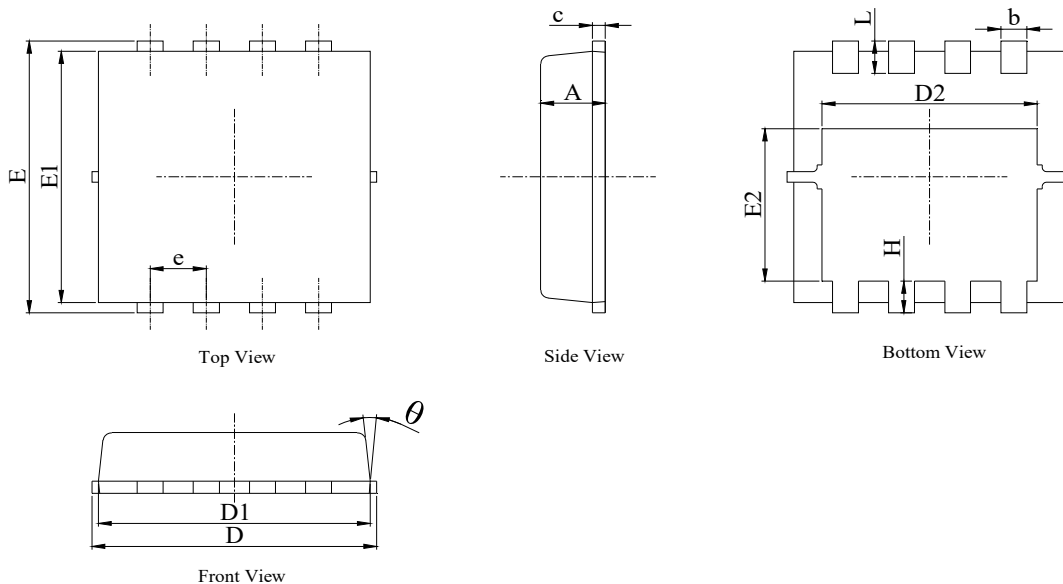
Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	55	65	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.5	4.5	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\mu\text{H}, V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

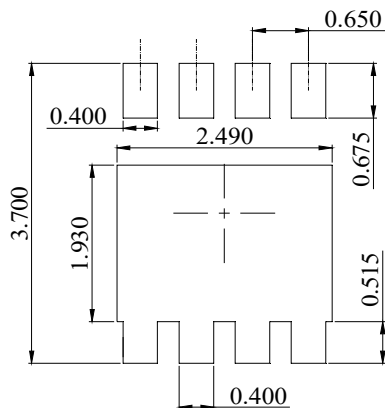
Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

Figure 7: Current De-rating

Figure 8: Power De-rating

Figure 9: Maximum Safe Operating Area

Figure 10: Single Pulse Power Rating, Junction-to-Case

Figure 11: Normalized Maximum Transient Thermal Impedance

PDFN3x3 Package Information
Package Outline

NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions $D1$ and $E1$ do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER	
	MIN.	MAX.
A	0.70	0.85
b	0.25	0.35
c	0.10	0.25
D	3.15	3.40
D1	3.00	3.25
D2	2.25	2.59
E	3.20	3.45
E1	3.00	3.22
E2	1.48	1.98
e	0.65 BSC	
H	0.30	0.58
L	0.25	0.50
θ	---	15°

Recommended Footprint


DIMENSIONS: MILLIMETERS

单击下面可查看定价，库存，交付和生命周期等信息

[>>JW\(捷捷微\)](#)